



## P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY								
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)					
- 12	$0.029$ at $V_{GS} = -4.5 \text{ V}$	- 12 <sup>a</sup>						
	$0.034 \text{ at V}_{GS} = -2.5 \text{ V}$	- 12 <sup>a</sup>	23 nC					
	0.044 at V <sub>GS</sub> = - 1.8 V	- 12 <sup>a</sup>	20110					
	0.100 at V <sub>GS</sub> = - 1.5 V	- 3						

# PowerPAK SC-70-6L-Single 2.05 mm 2.05 mm

#### Ordering Information:

SiA413DJ-T4-GE3 (Lead (Pb)-free and Halogen-free) SiA413DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

#### **FEATURES**

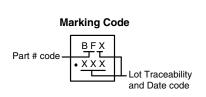
- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

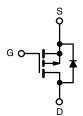


HALOGEN FREE

### **APPLICATIONS**

Load Switch, PA Switch and Battery Switch for Portable **Devices** 





P-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	<b>S</b> (T <sub>A</sub> = 25 °C, unle	ess otherwise not	ed)			
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	- 12	V		
Gate-Source Voltage		$V_{GS}$	± 8			
	T <sub>C</sub> = 25 °C		- 12 <sup>a</sup>			
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	$T_C = 70  ^{\circ}C$	I <sub>D</sub>	- 12 <sup>a</sup>			
(.g	T <sub>A</sub> = 25 °C	.0	- 10 <sup>b, c</sup>			
	T <sub>A</sub> = 70 °C		- 8 <sup>b, c</sup>	A		
Pulsed Drain Current		I <sub>DM</sub>	- 40			
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	- 12 <sup>a</sup>			
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	'S	- 2.9 <sup>b, c</sup>			
	T <sub>C</sub> = 25 °C		19			
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	P <sub>D</sub>	12	_ w		
	T <sub>A</sub> = 25 °C	ט י	3.5 <sup>b, c</sup>			
	T <sub>A</sub> = 70 °C		2.2 <sup>b, c</sup>			
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C			
Soldering Recommendations (Peak Temperature	e) <sup>d, e</sup>	•	260			

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5	O/ VV				

### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

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For more information please contact: pmostechsupport@vishay.com

www.vishay.com

# SiA413DJ

# Vishay Siliconix



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)									
Parameter	Symbol	Min.	Тур.	Max.	Unit				
Static									
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS}$ = 0 V, $I_D$ = - 250 $\mu A$	- 12			V			
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I <sub>D</sub> = - 250 μA		- 11					
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1 <sub>D</sub> = - 250 μΑ		2.7		mV/°C			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 0.4		- 1	V			
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA			
Zara Cata Valtaga Drain Current	1	V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V			- 1	^			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	- 10	μΑ					
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α			
		$V_{GS} = -4.5 \text{ V}, I_D = -6.7 \text{ A}$		0.024	0.029	+			
		$V_{GS} = -2.5 \text{ V}, I_D = -6.2 \text{ A}$		0.028	0.034	Ω			
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 2.3 A		0.036	0.044				
		V <sub>GS</sub> = - 1.5 V, I <sub>D</sub> = - 1 A		0.050	0.100	1			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 6.7 A		30		S			
Dynamic <sup>b</sup>				l					
Input Capacitance	C <sub>iss</sub>			1800		pF			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		450					
Reverse Transfer Capacitance	C <sub>rss</sub>			390					
T. 10 1 0		V <sub>DS</sub> = -6 V, V <sub>GS</sub> = -8 V, I <sub>D</sub> = -10 A		38	57				
Total Gate Charge	$Q_g$			23	35	nC			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -10 \text{ A}$		3					
Gate-Drain Charge	$Q_{gd}$			6.5					
Gate Resistance	$R_{g}$	f = 1 MHz		7		Ω			
Turn-On Delay Time	t <sub>d(on)</sub>			20	30				
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 6 V, $R_L$ = 0.75 $\Omega$		40	60				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 8 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		65	100				
Fall Time	t <sub>f</sub>			40	60				
Turn-On Delay Time	t <sub>d(on)</sub>			10	15	ns			
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 6 V, $R_L$ = 0.75 $\Omega$		12	20				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ - 8 A, $V_{GEN}$ = - 8 V, $R_g$ = 1 $\Omega$		70	105				
Fall Time	t <sub>f</sub>			40	60				
Drain-Source Body Diode Characteristi	cs			•	<b>'</b>	<b>'</b>			
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 12	Λ			
Pulse Diode Forward Current	I <sub>SM</sub>				40	Α			
Body Diode Voltage	$V_{SD}$	$I_S = -8 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t <sub>rr</sub>			40	60	ns			
Body Diode Reverse Recovery Charge	$Q_{rr}$	I <sub>F</sub> = - 8 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		20	30	nC			
Reverse Recovery Fall Time	t <sub>a</sub>	$I_F = -0$ A, $U_1/U_1 = 100$ A/ $\mu$ S, $I_J = 25$ °C		14					
Reverse Recovery Rise Time	t <sub>b</sub>			26		ns			

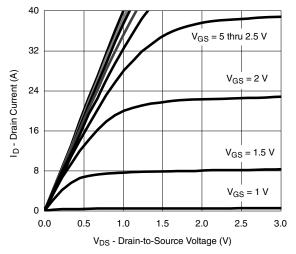
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

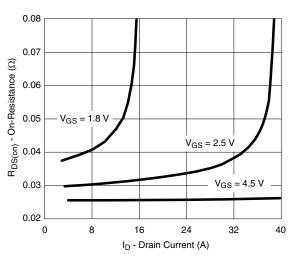




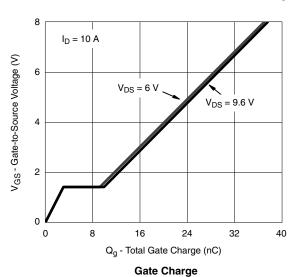
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

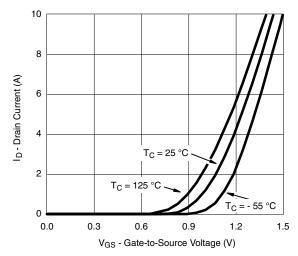


### **Output Characteristics**

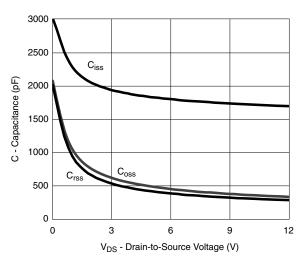


#### On-Resistance vs. Drain Current and Gate Voltage

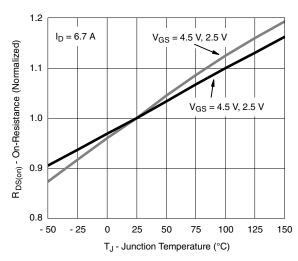




### **Transfer Characteristics**



#### Capacitance

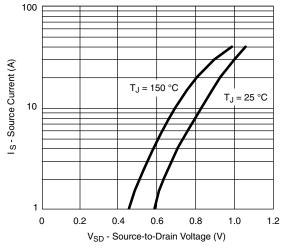


**On-Resistance vs. Junction Temperature** 

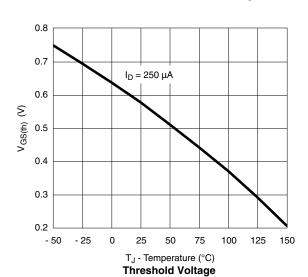
## Vishay Siliconix

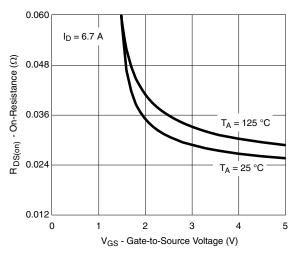
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## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

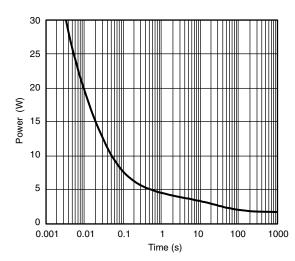


## Soure-Drain Diode Forward Voltage

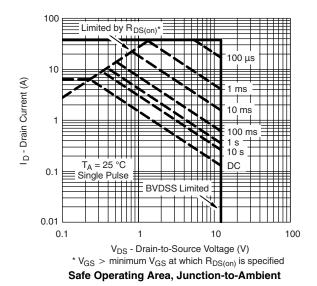




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

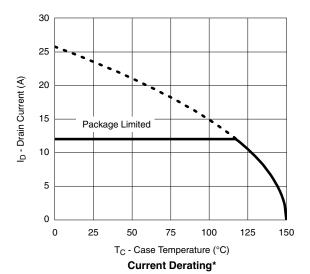


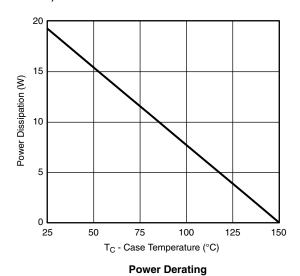






## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



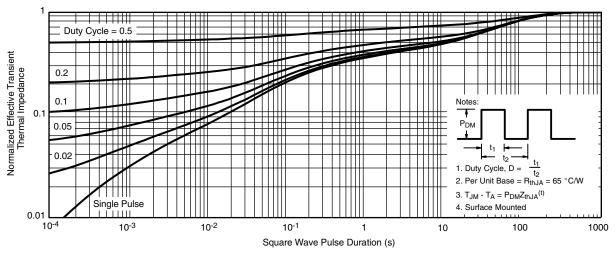


 $<sup>^{\</sup>star}$  The power dissipation P<sub>D</sub> is based on T<sub>J(max.)</sub> = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

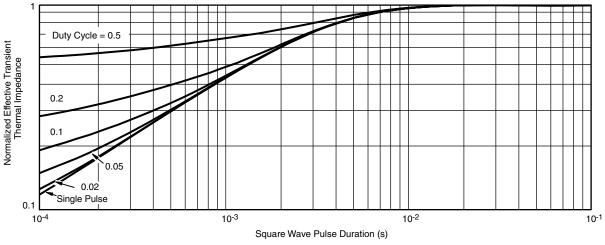
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## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



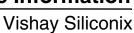
#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70447







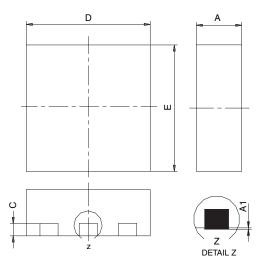
## PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
  Package outline exclusive of mold flash and metal burr
  Package outline inclusive of plating

			SINGL	E PAD		DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	ILLIMETER	RS		INCHES	
=	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
<b>A</b> 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;		0.65 BSC			0.026 BSC	
K		0.275 TYP	1		0.011 TYP	ı	0.275 TYP		0.011 TYP			
<b>K</b> 1		0.400 TYP	1	0.016 TYP		0.320 TYP		0.013 TYP				
K2		0.240 TYP	1	0.009 TYP		0.252 TYP		0.010 TYP				
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP	1	0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

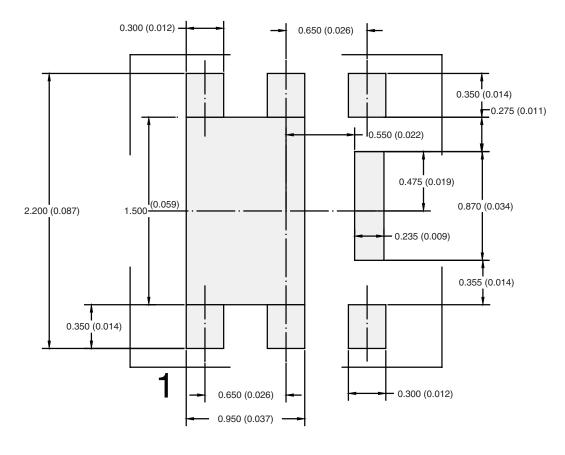
Document Number: 73001

06-Aug-07

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## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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